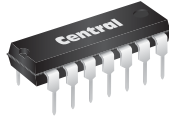


MPQ2222  
MPQ2222A

NPN SILICON QUAD TRANSISTOR



TO-116 CASE



www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR MPQ2222 and MPQ2222A types are comprised of four independent NPN silicon transistors mounted in a 14-pin DIP, designed for general purpose amplifier and switching applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage  
Collector-Emitter Voltage  
Emitter-Base Voltage  
Continuous Collector Current  
Power Dissipation (per transistor)  
Power Dissipation (total package)  
Operating and Storage Junction Temperature  
Thermal Resistance (total package)

SYMBOL	MPQ2222	MPQ2222A	UNITS
$V_{CBO}$	60	75	V
$V_{CEO}$	40	40	V
$V_{EBO}$	5.0	6.0	V
$I_C$		500	mA
$P_D$		650	mW
$P_D$		1.9	W
$T_J, T_{stg}$		-65 to +150	$^\circ\text{C}$
$\Theta_{JA}$		66	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$ )

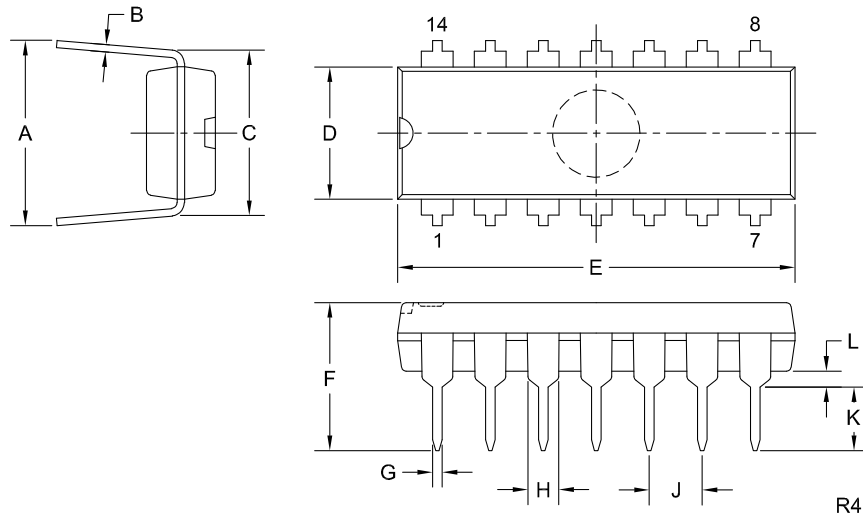
SYMBOL	TEST CONDITIONS	MPQ2222		MPQ2222A		UNITS
		MIN	MAX	MIN	MAX	
$I_{CBO}$	$V_{CB}=50\text{V}$	-	50	-	-	nA
$I_{CBO}$	$V_{CB}=60\text{V}$	-	-	-	10	nA
$I_{EBO}$	$V_{EB}=3.0\text{V}$	-	100	-	100	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	60	-	75	-	V
$BV_{CEO}$	$I_C=10\text{mA}$	40	-	40	-	V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0	-	6.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.4	-	0.3	V
$V_{CE(SAT)}$	$I_C=300\text{mA}, I_B=30\text{mA}$	-	1.6	-	-	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	-	-	1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.3	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=300\text{mA}, I_B=30\text{mA}$	-	2.6	-	-	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	-	-	2.0	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	-	-	35	-	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	-	-	50	-	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75	-	75	-	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	100	300	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=300\text{mA}$	30	-	-	-	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	-	-	40	-	
$f_T$	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	200	-	200	-	MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$	-	8.0	-	8.0	pF
$C_{ib}$	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$	-	30	-	30	pF
$t_r$	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	-	-	35	ns
$t_s$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	-	-	285	ns

R3 (27-September 2021)

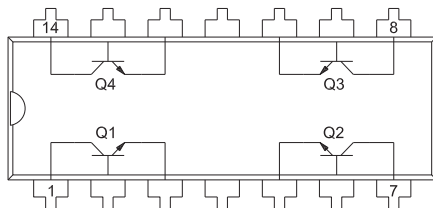
MPQ2222  
MPQ2222A  
  
NPN SILICON QUAD TRANSISTOR



**TO-116 CASE - MECHANICAL OUTLINE**



**PIN CONFIGURATION**



**LEAD CODE:**

- |                  |                   |
|------------------|-------------------|
| 1) Collector Q1  | 8) Collector Q3   |
| 2) Base Q1       | 9) Base Q3        |
| 3) Emitter Q1    | 10) Emitter Q3    |
| 4) No Connection | 11) No Connection |
| 5) Emitter Q2    | 12) Emitter Q4    |
| 6) Base Q2       | 13) Base Q4       |
| 7) Collector Q2  | 14) Collector Q4  |

**MARKING: FULL PART NUMBER**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.310	0.390	7.9	9.9
B	0.008	0.014	0.2	0.4
C	0.310		7.9	
D	0.240	0.260	6.1	6.6
E	0.740	0.760	18.8	19.3
F	0.300		7.6	
G	0.014	0.022	0.4	0.6
H	0.050		1.3	
J	0.100		2.5	
K	0.125	0.150	3.2	3.8
L	0.015	-	0.4	-

TO-116 (REV: R4)

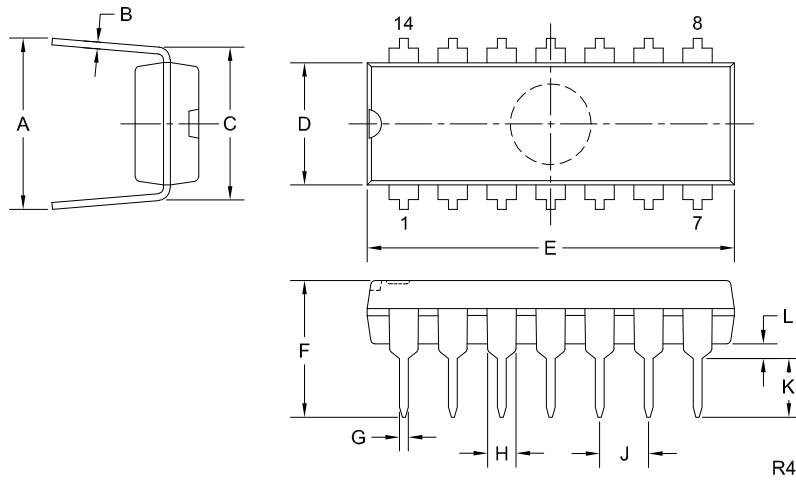
R3 (27-September 2021)

# Package Details

## TO-116



### Mechanical Drawing



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.310	0.390	7.9	9.9
B	0.008	0.014	0.2	0.4
C	0.310		7.9	
D	0.240	0.260	6.1	6.6
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F	0.300		7.6	
G	0.014	0.022	0.4	0.6
H	0.050		1.3	
J	0.100		2.5	
K	0.125	0.150	3.2	3.8
L	0.015	-	0.4	-

TO-116 (REV: R4)

### Packing Options

#### Bulk - Packing Code: C

C = Antistatic coated plastic sleeve (surface resistivity of  $>10^9$  and  $<10^{13}$  ohms per square).

**Bulk Packing Quantity: 25**

R4 (11-February 2021)

# Material Composition Specification

## TO-116 Case



Device average mass . . . . . 1035 mg  
 Fluctuation margin . . . . . +/-10%

Component	Material	Material		Substance	CAS No.	Substance		
		(%wt)	(mg)			(%wt)	(mg)	(ppm)
active device	doped Si	0.05%	0.5	Si	7440-21-3	0.048%	0.5	483
bond wire	gold	0.02%	0.21	Au	7440-57-5	0.02%	0.21	203
leadframe	Cu alloy 194 w/ silver plating	32.85%	340	Cu	7440-50-8	31.981%	331	319,807
				Fe	7439-89-6	0.773%	8	7,729
				Zn	7440-66-6	0.043%	0.45	435
				P	7723-14-0	0.035%	0.36	348
				Ag	7440-22-4	0.018%	0.19	184
die attach	silver epoxy	0.03%	0.29	Ag	7440-22-4	0.022%	0.23	222
				epoxy resin	9003-36-5	0.003%	0.03	29
				diluent	26647-14-3	0.002%	0.02	19
				hardener	620-92-8	0.001%	0.01	10
encapsulation*	EMC	65.89%	682	silica	7631-86-9	52.715%	545.6	527,150
				epoxy resin	Proprietary	9.884%	102.3	98,841
				TBBA	79-94-7	1.652%	17.1	16,522
				Sb <sub>2</sub> O <sub>3</sub>	1309-64-4	1.314%	13.6	13,140
				carbon black	1333-86-4	0.329%	3.4	3,285
	EMC GREEN	65.89%	682	silica (fused)	60676-86-0	56.01%	579.7	560,097
				epoxy resin	Proprietary	4.193%	43.4	41,932
				phenol resin	9003-35-4	4.193%	43.4	41,932
				epoxy, cresol novolac	29690-82-2	1.314%	13.6	13,140
				carbon black	1333-86-4	0.184%	1.9	1,836
plating**	tin/lead process	1.16%	12	Sn	7440-31-5	0.928%	9.6	9,275
				Pb	7439-92-1	0.232%	2.4	2,319
	matte tin	1.16%	12	Sn	7440-31-5	1.159%	12	11,594

\*EMC GREEN molding compound is Halogen-Free.

\*\*For Lead Free plating, add suffix "PB FREE" to part number.

For Tin/Lead plating, add suffix "TIN/LEAD" to part number.

No suffix designation allows for the supply of either lead-free or tin/lead plated product depending on availability.

**Disclaimer**

The information provided in this Material Composition data sheet is, to the best of our knowledge, correct. However, there is no guarantee to completeness or accuracy, as some information is derived from data sources outside the company.

R2 (16-July 2018)